AUTOMOTIVE GRADE

RoHS

COMPLIANT

HALOGEN

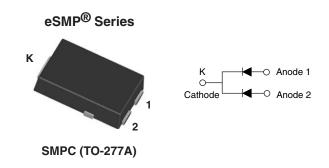
FREE



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Vishay Semiconductors

Hyperfast Rectifier, 2 x 3 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 x 3 A			
V _R	200 V			
V _F at I _F	0.75 V			
t _{rr (typ.)}	27 ns			
T _J max.	175 °C			
Package	SMPC (TO-277A)			
Circuit configuration	Common cathode			

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMPC (TO-277A)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V_{RRM}		200	V
Average rectified forward current -	per device	_	T _ 165 °C	6	
Average rectilled forward current -	per diode	I _{F(AV)}	T _{Sp} = 165 °C	3	۸
Non-repetitive peak surge current -	per device	_	T _{.I} = 25 °C, 6 ms square pulse	150	А
per diode		IFSM	r _J = 25 °C, o ms square pulse	80	
Operating junction and storage terr	peratures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	
Forward voltage, per diode	V _F	I _F = 3 A	-	0.87	0.94	V
		I _F = 3 A, T _J = 125 °C	-	0.75	0.79	
Reverse leakage current, per diode	I _R	$V_R = V_R$ rated	-	-	2	
		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	2	10	μA
Junction capacitance	C _T	V _R = 200 V	-	12	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST C	TEST CONDITIONS		TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		27	=	
Poverne receivent time		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25	200
Reverse recovery time	t _{rr}	T _J = 25 °C		-	20	-	ns
		T _J = 125 °C		-	26	-	
Peak recovery current I _{RRM}	,	T _J = 25 °C	$I_F = 3 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	2.4	-	Α
	IRRM	T _J = 125 °C		-	3.8	-	_ ^
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	23	-	nC
	T _J = 125 °C]	-	50	-		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to mount, per diode	R _{thJM}		-	2.8	4	°C/W
Approximate weight				0.1		g
Approximate weight				0.0035		oz.
Marking device		Case style SMPC (TO-277A)	NCH2			

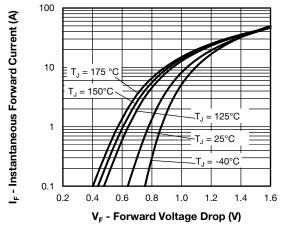


Fig. 1 - Typical Forward Voltage Drop Characteristics

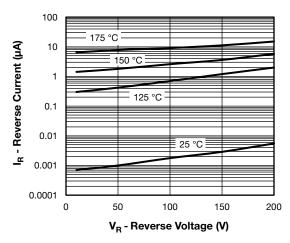


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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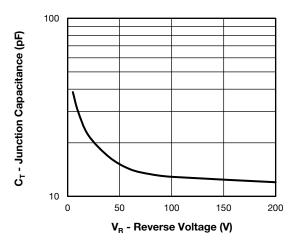


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

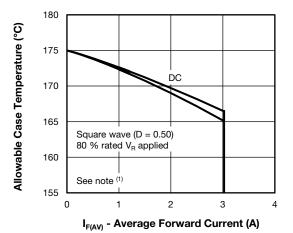


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

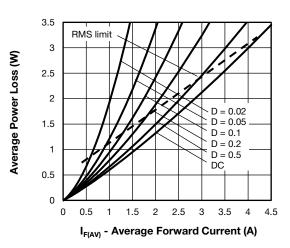


Fig. 5 - Forward Power Loss Characteristics

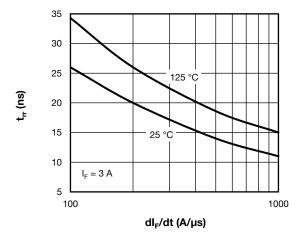


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

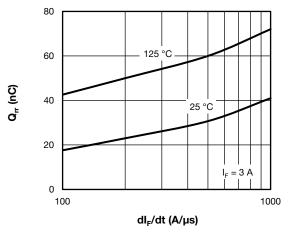


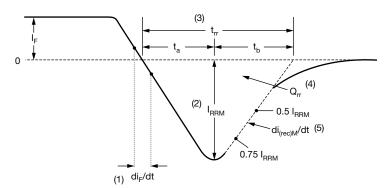
Fig. 7 - Typical Stored Charge vs. dI_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (\text{Pd} + \text{Pd}_{\text{REV}}) \times \text{R}_{\text{thJC}}; \\ \text{Pd} = \text{forward power loss} = I_{\text{F(AV)}} \times \text{V}_{\text{FM}} \text{ at } (I_{\text{F(AV)}}/\text{D}) \text{ (see fig. 5)}; \\ \text{Pd}_{\text{REV}} = \text{inverse power loss} = \text{V}_{\text{R1}} \times \text{I}_{\text{R}} \text{ (1 - D)}; I_{\text{R}} \text{ at } \text{V}_{\text{R1}} = \text{rated V}_{\text{R}} \\ \end{array}$

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{rr}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \boldsymbol{Q}_{rr} area under curve defined by \boldsymbol{t}_{rr} and \boldsymbol{I}_{RRM}

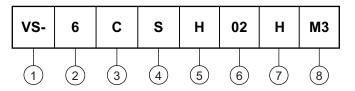
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 Current rating (6 = 6 A)
- Circuit configuration:

C = common cathode

- S = SMPC package

5 - Process type,

H = hyper fast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-6CSH02HM3/86A	1500	1500	7" diameter plastic tape and reel			
VS-6CSH02HM3/87A	6500	6500	13" diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95570</u>				
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96378			

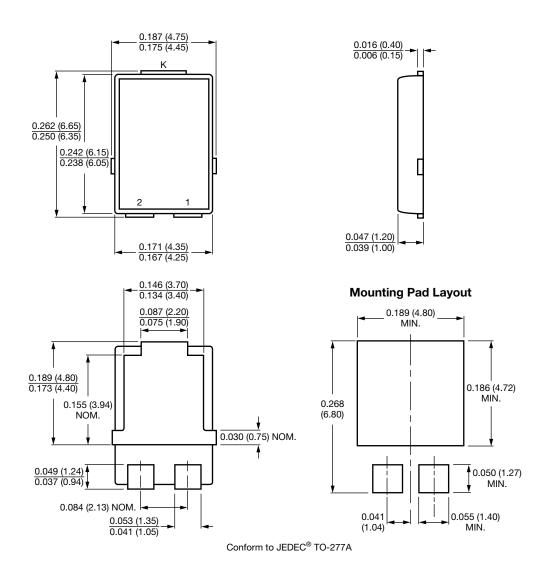
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SMPC (TO-277A)

DIMENSIONS in inches (millimeters)



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